

PATENT ABSTRACTS OF JAPAN

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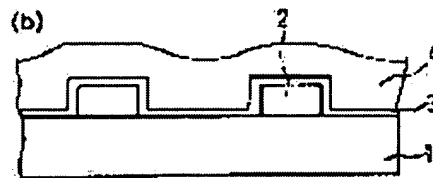
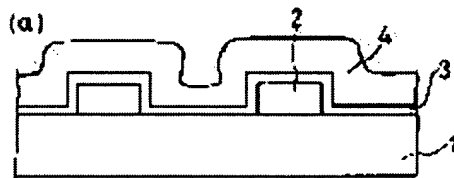
(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To prevent a lower layer insulating film from flowing during reflow of an upper layer insulating film by forming a humidity-resistant film to cover a metallic wiring film on the layer insulating film of a first layer and by forming and reflowing a layer insulating film of the second layer thereon.

CONSTITUTION: A layer insulating film (BPSG film) 1 of a first layer is flattened by reflow and a metallic wiring film 2 is formed on the flatten BPSG film 1. A BPSG film 4 of a second layer is formed on the first BPSG film 1 to cover the metallic wiring film 2 and the second BPSG film 4 is flattened by reflow. A silicon nitride film 3 is formed on the first BPSG film 1 as a humidity-resistant film before formation of the second BPSG film 4.

Thereby, vapor in reflow atmosphere does not enter the lower BPSG film 1 during reflow of the upper BPSG film 4 and the lower BPSG film 1 is prevented from flowing.



LEGAL STATUS

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